

# PMEG2010AEJ

20 V, 1 A very low  $V_F$  MEGA Schottky barrier rectifier in SOD323F package

Rev. 01 — 2 March 2005

**Product data sheet** 



### 1. Product profile

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in a SOD323F (SC-90) very small and flat SMD plastic package.

#### 1.2 Features

Forward current: 1 A

Reverse voltage: 20 V

- Very low forward voltage
- Very small and flat SMD package

### 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Voltage clamping
- Inverse polarity protection
- Low and medium power general applications

#### 1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F</sub>	forward current	$T_{sp} \le 55  ^{\circ}C$	-	-	1	Α
$V_R$	reverse voltage		-	-	20	V
V <sub>F</sub>	forward voltage	$I_F = 1000 \text{ mA}$	<u>[1]</u> -	480	550	mV

[1] Pulse test:  $t_0 \le 300 \,\mu\text{s}$ ;  $\delta \le 0.02$ .



## 2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	
2	anode	1 2	1 🕂 2
			sym001

<sup>[1]</sup> The marking bar indicates the cathode.

### 3. Ordering information

**Table 3: Ordering information** 

Type number	Package		
	Name	Description	Version
PMEG2010AEJ	SC-90	plastic surface mounted package; 2 leads	SOD323F

# 4. Marking

Table 4: Marking codes

Type number	Marking code
PMEG2010AEJ	EM

## 5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage		-	20	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 55 °C	-	1	А
$I_{FRM}$	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	5.5	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8 ms square wave	<u>[1]</u> _	10	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	0.36	mW
			[2]	0.83	mW
Tj	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-65	+150	°C
$T_{stg}$	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1][2]	-	350	K/W
			[1][3]	-	150	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	55	K/W

<sup>[1]</sup> For Schottky barrier diodes thermal run-away has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses. Nomograms for determining the reverse power losses  $P_R$  and  $I_{F(AV)}$  rating will be available on request.

### 7. Characteristics

**Table 7: Characteristics** 

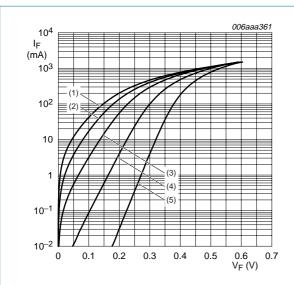
 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	see Figure 1;	<u>[1]</u>			
		I <sub>F</sub> = 10 mA	-	240	270	mV
		I <sub>F</sub> = 100 mA	-	300	350	mV
		I <sub>F</sub> = 500 mA	-	400	460	mV
		I <sub>F</sub> = 1000 mA	-	480	550	mV
I <sub>R</sub>	reverse current	see Figure 2;				
		$V_R = 5 V$	-	5	10	μΑ
		$V_R = 8 V$	-	7	20	μΑ
		$V_R = 10 V$	-	8	30	μΑ
		$V_{R} = 15 \text{ V}$	-	10	50	μΑ
		$V_R = 20 V$	-	15	70	μΑ
C <sub>d</sub>	diode	$V_R = 1 V$ ; $f = 1 MHz$ ;	-	40	50	pF
	capacitance	see Figure 3				

<sup>[1]</sup> Pulse test:  $t_0 \le 300 \,\mu\text{s}$ ;  $\delta \le 0.02$ .

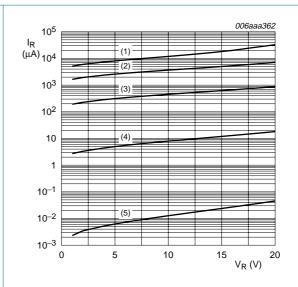
<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.



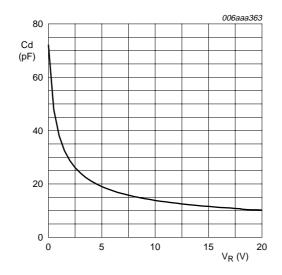
- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 125 \, ^{\circ}C$
- (3)  $T_{amb} = 85 \, ^{\circ}C$
- (4)  $T_{amb} = 25 \, ^{\circ}C$
- (5)  $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 125 \,^{\circ}C$
- (3)  $T_{amb} = 85 \, ^{\circ}C$
- (4)  $T_{amb} = 25 \, ^{\circ}C$
- (5)  $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$ 

Fig 3. Diode capacitance as a function of reverse voltage; typical values

### 8. Package outline

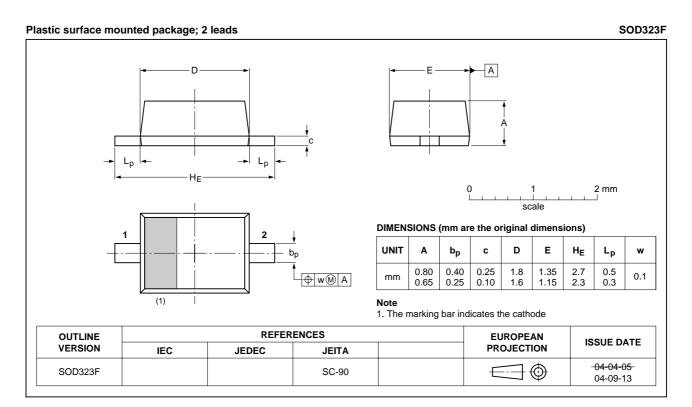


Fig 4. Package outline SOD323F (SC-90)

# 9. Packing information

#### Table 8: Packing methods

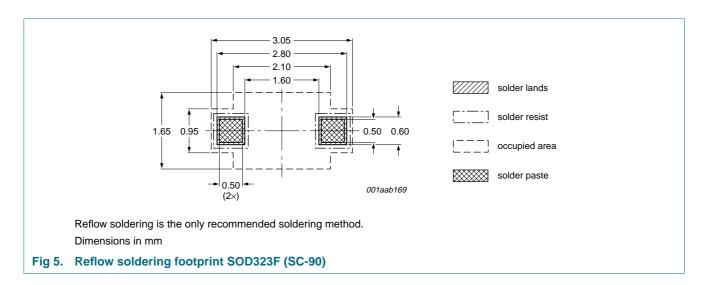
The -xxx numbers are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG2010AEJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see  $\underline{\text{Section 15}}$ .

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# 10. Soldering







# 11. Revision history

### Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PMEG2010AEJ_1	20050302	Product data sheet	-	9397 750 14595	-

#### 12. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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- [2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

### 13. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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For sales office addresses, send an email to: <a href="mailto:sales.addresses@www.semiconductors.philips.com">sales.addresses@www.semiconductors.philips.com</a>

### **Philips Semiconductors**

# PMEG2010AEJ

20 V, 1 A very low V<sub>F</sub> MEGA Schottky barrier rectifier

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